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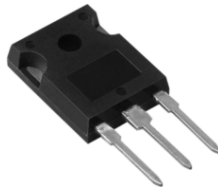
sales@integrated-circuit.com



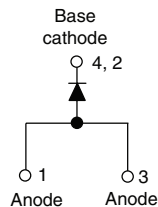
80EPS.. High Voltage Series

Vishay High Power Products

Input Rectifier Diode, 80 A



TO-247AC



DESCRIPTION/FEATURES

The 80EPS.. rectifier High Voltage Series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.

Typical applications are in input rectification and these products are designed to be used with Vishay HPP switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

PRODUCT SUMMARY

V_F at 80 A	1.17 V
I_{FSM}	1450 A
V_{RRM}	800/1200 V

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Sinusoidal waveform	80	A
V_{RRM}	Range	800/1200	V
I_{FSM}		1450	A
V_F	80 A, $T_J = 25\text{ }^\circ\text{C}$	1.17	V
T_J		- 40 to 150	$^\circ\text{C}$

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} AT 150 °C mA
80EPS08	800	900	1
80EPS12	1200	1300	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	$T_C = 100\text{ }^\circ\text{C}$, 180° conduction half sine wave	80	A
Maximum peak one cycle non-repetitive surge current	I_{FSM}	10 ms sine pulse, rated V_{RRM} applied	1450	
		10 ms sine pulse, no voltage reapplied	1500	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	10 500	A^2s
		10 ms sine pulse, no voltage reapplied	14 000	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to } 10\text{ ms}$, no voltage reapplied	105 000	$\text{A}^2\sqrt{\text{s}}$

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ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V_{FM}	80 A, $T_J = 25\text{ }^\circ\text{C}$		1.17	V
Forward slope resistance	r_f	$T_J = 150\text{ }^\circ\text{C}$		3.17	$\text{m}\Omega$
Threshold voltage	$V_{F(TO)}$			0.73	V
Maximum reverse leakage current	I_{RM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}$	0.1	mA
		$T_J = 150\text{ }^\circ\text{C}$		1.0	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}			- 40 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		0.35	$^\circ\text{C/W}$
Maximum thermal resistance, junction to ambient	R_{thJA}			40	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased		0.2	
Approximate weight				6	g
				0.21	oz.
Mounting torque	minimum			6 (5)	kgf · cm (lbf · in)
	maximum			12 (10)	
Marking device		Case style TO-247AC (JEDEC)		80EPS08	
				80EPS12	



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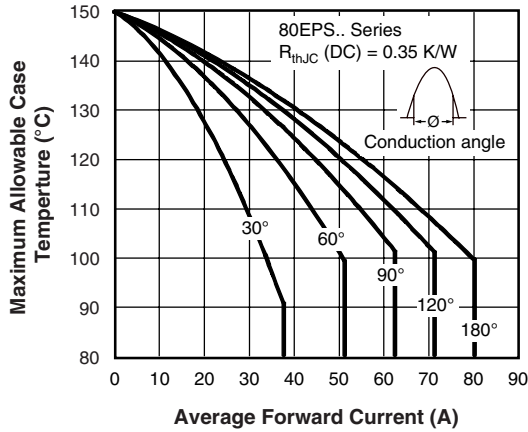


Fig. 1 - Current Rating Characteristics

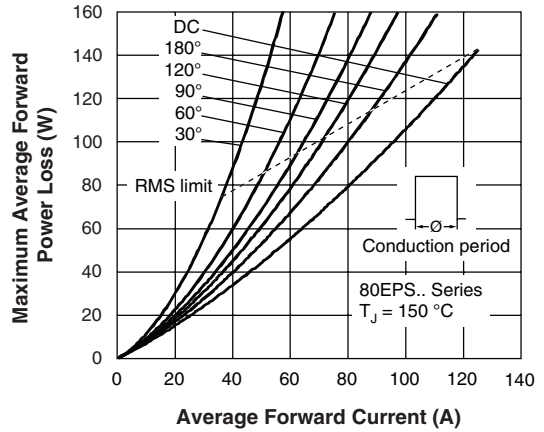


Fig. 4 - Forward Power Loss Characteristics

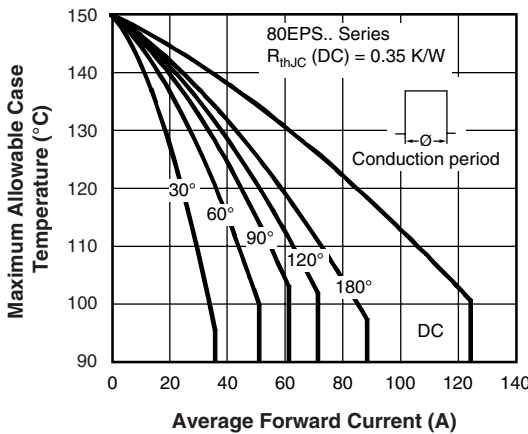


Fig. 2 - Current Rating Characteristics

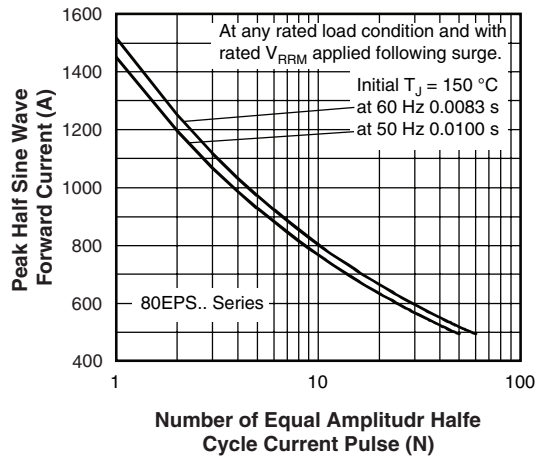


Fig. 5 - Maximum Non-Repetitive Surge Current

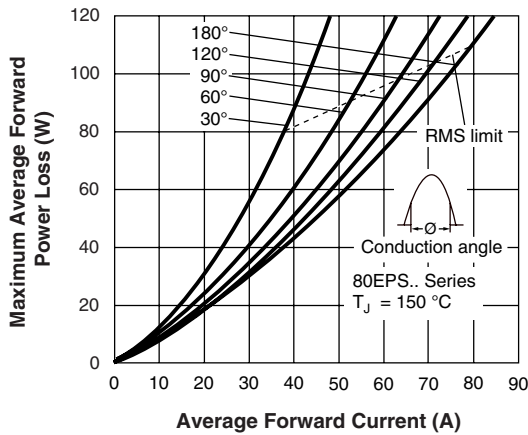


Fig. 3 - Forward Power Loss Characteristics

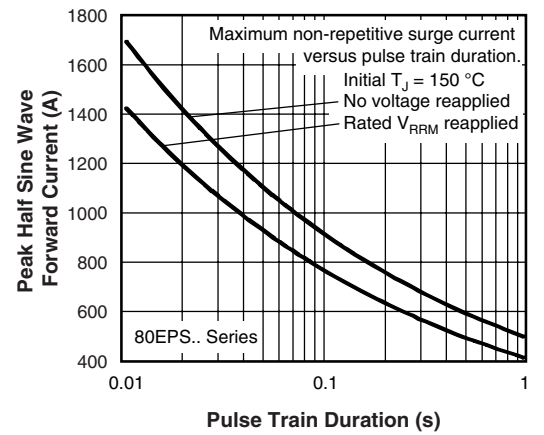


Fig. 6 - Maximum Non-Repetitive Surge Current

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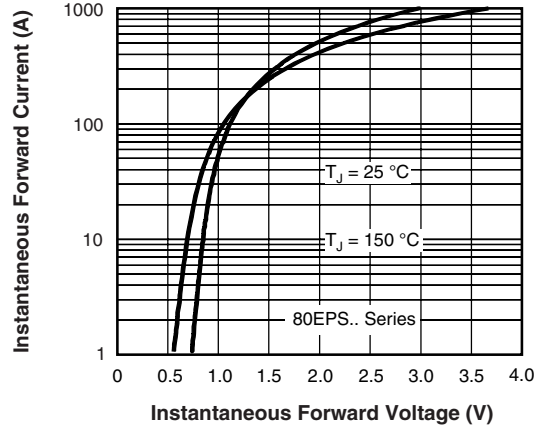


Fig. 7 - Forward Voltage Drop Characteristics

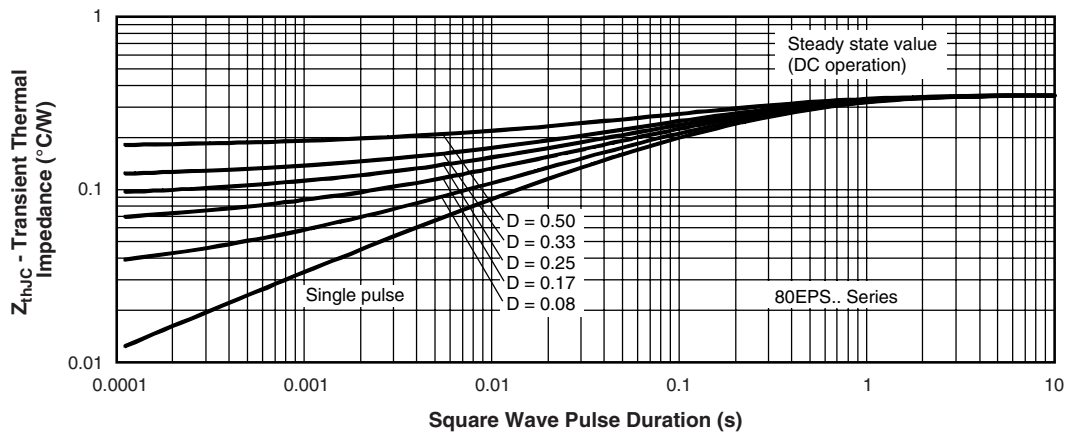


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



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ORDERING INFORMATION TABLE

Device code	80	E	P	S	12	-
	①	②	③	④	⑤	⑥
	1	-	Current rating (80 = 80 A)			
	2	-	Circuit configuration:			
			E = Single diode			
	3	-	Package:			
			P = TO-247AC			
	4	-	Type of silicon:			
			S = Standard recovery rectifier			
	5	-	Voltage ratings			
						08 = 800 V 12 = 1200 V
	6	-	• None = Standard production			
			• PbF = Lead (Pb)-free			

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95223
Part marking information	www.vishay.com/doc?95226



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Vishay

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